



THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of: )  
ZENG )  
Serial No. 09/844,347 )  
Confirmation No. 2463 )  
Filing Date: April 27, 2001 )  
For: POWER MOSFET AND METHOD FOR )  
FORMING SAME USING A SELF- )  
ALIGNED BODY IMPLANT )

#11/Amendt B  
(AF)  
Q Fored  
11/15/02

Examiner: I. SOWARD

Art Unit: 2822

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AMENDMENT AFTER FINAL

Box AF  
Director, U.S. Patent and Trademark Office  
Washington, D.C. 20231

Sir:

Responsive to the Examiner's final Office Action of September 5, 2002, please enter the amendments and remarks set forth below. No new issues are raised by this amendment.

In the Claims:

The claims have been amended as follows:

23. (Twice Amended) A MOSFET comprising:  
a semiconductor layer having a trench therein;  
a gate conducting layer in a lower portion of the  
trench;

a dielectric layer in an upper portion of the trench  
and extending outwardly from said semiconductor layer;  
source regions adjacent the outwardly extending  
dielectric layer; and  
source/body contact regions laterally spaced apart  
from said gate conducting layer and non-interruptibly

Select

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